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Gallium Nitride Materials and Devices V

**Jen-Inn Chyi
Yasushi Nanishi
Hadis Morkoç
Cole W. Litton
Joachim Piprek
Euijoon Yoon**
Editors

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Contents

ix	Conference Committee
xi	Dedication to Dr. Cole W. Litton
xiii	Introduction

GROWTH I

7602 02	Growth of self-standing GaN substrates (Invited Paper) [7602-01] H.-J. Lee, K. Fujii, T. Goto, Tohoku Univ. (Japan); C. Kim, Kyunghee Univ. (Korea, Republic of); J. Chang, Korea Maritime Univ. (Korea, Republic of); S.-K. Hong, Chungnam National Univ. (Korea, Republic of); M. Cho, Wavesquare Inc. (Korea, Republic of); T. Yao, Tohoku Univ. (Japan)
7602 03	Selective growth and impurity incorporation in semipolar GaN grown on Si substrate (Invited Paper) [7602-02] N. Sawaki, Aichi Institute of Technology (Japan) and Nagoya Industrial Science Research Institute (Japan); Y. Honda, T. Hikosaka, S. Tanaka, M. Yamaguchi, N. Koide, K. Tomita, Nagoya Univ. (Japan)

GROWTH II

7602 0A	Molecular beam epitaxial growth, fabrication, and characterization of InN/Si nanowire heterojunction solar cells [7602-09] Y.-L. Chang, Z. Mi, McGill Univ. (Canada)
7602 0B	The comprehensive characteristics of quaternary AlInGaN with various TMI molar rate [7602-10] S.-F. Yu, S.-J. Chang, S.-P. Chang, National Cheng Kung Univ. (Taiwan); R.-M. Lin, Chang Gung Univ. (Taiwan)

GROWTH III

7602 0C	Ammonothermal growth of GaN substrates (Invited Paper) [7602-11] R. Dwiliński, R. Doradziński, J. Garczyński, L. Sierżputowski, R. Kucharski, M. Zajac, Ammono Sp. z o.o. (Poland); M. Rudziński, W. Strupiński, Institute of Electronic Materials Technology (Poland); J. Serafińczuk, R. Kudrawiec, Wrocław Univ. of Technology (Poland)
7602 0D	Non-polar m-plane GaN film and polarized InGaN/GaN LED grown on LiAlO₂ (001) substrates (Invited Paper) [7602-12] R. Zhang, Z. L. Xie, B. Liu, X. Q. Xiu, D. Y. Fu, Z. Zhang, P. Han, Y. D. Zheng, Nanjing Univ. (China); S. M. Zhou, Shanghai Institute of Optics and Fine Mechanics (China)
7602 0E	Magnetic cages of GaN nanoclusters doped with Gd and Nd [7602-13] V. Kumar, Dr. Vijay Kumar Foundation (India); J. M. Zavada, U.S. Army Research Office (United States)

- 7602 OG **Extended defects in semipolar (11-22) gallium nitride** [7602-15]
Y. Arroyo-Rojas Dasilva, P. Ruterana, CIMAP, CNRS-ENSICAEN-CEA-UCBN (France);
L. Lahourcade, E. Monroy, INAC/SP2M/PSC (France); G. Nataf, CRHEA, CNRS (France)

FETS

- 7602 OH **Plasmon-assisted dissipation of LO-mode heat in nitride 2DEG channels** [7602-16]
A. Matulionis, J. Liberis, Puslaidininkiu Fizikos Institutas (Lithuania); H. Morkoç, Virginia Commonwealth Univ. (United States)
- 7602 OI **InGaN light-emitting diodes with highly transparent ZnO:Ga electrodes** [7602-79]
H. Y. Liu, X. Li, X. Ni, V. Avrutin, N. Izyumskaya, Ü. Özgür, H. Morkoç, Virginia Commonwealth Univ. (United States)
- 7602 OK **Transmission electron microscopy and XRD investigations of InAlN/GaN thin heterostructures for HEMT applications** [7602-19]
A. Vilalta-Clemente, M. Morales, M. P. Chauvat, Y. Arroyo-Rojas Dasilva, CIMAP, CNRS-ENSICAEN-CEA-UCBN (France); M. A. Poisson, Alcatel-Thales III-V Lab. (France); M. Heuken, C. Giesen, AIXTRON AG (Germany); P. Ruterana, CIMAP, CNRS-ENSICAEN-CEA-UCBN (France)

FET RELIABILITY

- 7602 OL **Quantum 1/f noise theory and experiment in QWIPs** [7602-20]
A. M. Truong, P. H. Handel, Univ. of Missouri-St. Louis (United States)
- 7602 OM **1/f noise: a window to HFET stability** [7602-21]
P. H. Handel, T. Sherif, Univ. of Missouri-St. Louis (United States); C. Kayis, J. Leach, C. Zhu, H. Morkoç, Virginia Commonwealth Univ. (United States)
- 7602 ON **Analytical calculation of the quantum 1/f coherence parameter for HFETs** [7602-22]
P. H. Handel, T. S. Sherif, Univ. of Missouri-St. Louis (United States)
- 7602 OO **Measurements of gate lag in high-quality nearly lattice matched InAlN/AlN/GaN HFET structures** [7602-23]
J. H. Leach, M. Wu, X. Ni, X. Li, Ü. Özgür, H. Morkoç, Virginia Commonwealth Univ. (United States)

ADVANCED TECHNIQUES I

- 7602 OQ **Nano-ultrasonic based on GaN nano-layers (Invited Paper)** [7602-25]
C.-K. Sun, National Taiwan Univ. (Taiwan) and Research Ctr. for Applied Sciences (Taiwan); Y.-C. Wen, Y.-H. Chen, National Taiwan Univ. (Taiwan); K.-H. Lin, Industrial Technology Research Institute South (Taiwan)
- 7602 OT **Scanning near-field optical spectroscopy of AlGaIn-based light emitting diodes** [7602-28]
A. Pinos, S. Marcinkevičius, Royal Institute of Technology (Sweden)

- 7602 0U **Thermal conductivity measurement of pulsed-MOVPE InN alloy grown on GaN/Sapphire by 3ω method** [7602-29]
H. Tong, J. Zhang, H. Zhao, G. Liu, V. A. Handara, J. A. Herbsommer, N. Tansu, Lehigh Univ. (United States)

ADVANCED TECHNIQUES II

- 7602 0Y **Effect of UV exposure on the surface charge behavior for GaN** [7602-33]
M. Foussekis, J. D. Ferguson, X. Ni, H. Morkoç, M. A. Reshchikov, A. A. Baski, Virginia Commonwealth Univ. (United States)
- 7602 0Z **Achieving p-In_xGa_{1-x}N alloys with high In contents** [7602-34]
B. N. Pantha, A. Sedhain, J. Li, J. Y. Lin, H. X. Jiang, Texas Tech Univ. (United States)

QW AND DOTS

- 7602 12 **Extended defects in nitride layers, influence on the quantum wells and quantum dots (Invited Paper)** [7602-37]
P. Ruterana, M. P. Chauvat, Y. Arroyo Rojas Dasilva, H. Lei, CIMAP, CNRS-ENSICAEN-CEA-UCBN (France); L. Lahourcade, E. Monroy, INAC/SP2M/PSC (France)

LASERS

- 7602 15 **The lasing characteristics of GaN-based two-dimensional photonic crystal surface-emitting lasers (Invited Paper)** [7602-40]
S. W. Chen, T. T. Kao, T. T. Wu, T. C. Lu, H. C. Kuo, S. C. Wang, National Chiao Tung Univ. (Taiwan)
- 7602 17 **GaN-based VCSELs: analysis of internal device physics and performance limitations** [7602-42]
J. Piprek, NUSOD Institute LLC (United States); S. Li, Crosslight Software Inc. (Canada)
- 7602 18 **High-power high-efficiency continuous-wave InGaN laser diodes in the violet, blue, and green wavelength regimes** [7602-43]
J. W. Raring, E. M. Hall, M. C. Schmidt, C. Poblentz, B. Li, N. Pfister, D. F. Feezell, R. Craig, J. S. Speck, S. P. DenBaars, S. Nakamura, Kaai, Inc. (United States)
- 7602 19 **Performance improvement of InGaN-based laser diodes by epitaxial layer structure design** [7602-44]
J. Liu, Y. Zhang, Z. Lochner, S.-S. Kim, Georgia Institute of Technology (United States); H. Kim, Chonbuk National Univ. (Korea, Republic of); J.-H. Ryou, S.-C. Shen, P. D. Yoder, R. D. Dupuis, Georgia Institute of Technology (United States); Q. Wei, K. Sun, A. Fischer, F. Ponce, Arizona State Univ. (United States)

NOVEL DEVICES

- 7602 1A **Review of nitride infrared intersubband devices (Invited Paper)** [7602-45]
M. Tchernycheva, F. H. Julien, Institut d'Electronique Fondamentale, CNRS, Univ. Paris-Sud 11 (France); E. Monroy, Commissariat à l'Énergie Atomique (France)
- 7602 1B **First-principles simulation of GaN material and devices: an application to GaN APDs (Invited Paper)** [7602-46]
E. Bellotti, M. Moresco, Boston Univ. (United States); F. Bertazzi, Boston Univ. (United States) and Politecnico di Torino (Italy)
- 7602 1E **Promising composite die-bonding materials for high-power GaN-based LED applications** [7602-50]
R.-H. Horng, National Cheng Kung Univ. (Taiwan); J.-S. Hong, Y.-L. Tsai, C.-J. Chen, C.-M. Chen, D.-S. Wu, National Chung Hsing Univ. (Taiwan)

LEDS I

- 7602 1F **Realization of high-efficiency AlGaIn-based ultraviolet light emitters (Invited Paper)** [7602-51]
S.-R. Jeon, S.-J. Lee, I.-K. Kang, J. B. Kim, N. Hwang, Korea Photonics Technology Institute (Korea, Republic of); S.-J. Son, LG Innotek (Korea, Republic of)
- 7602 1G **Novel device concepts for high-efficiency InGaIn-based light-emitting diodes (Invited Paper)** [7602-52]
H. Zhao, G. Liu, Y.-K. Ee, X.-H. Li, H. Tong, J. Zhang, G. S. Huang, N. Tansu, Lehigh Univ. (United States)
- 7602 1H **Role of interface roughness on lateral transport in InGaIn/GaN LEDs: diffusion length, dislocation spacing, and radiative efficiency** [7602-53]
I.-L. Lu, Y.-R. Wu, National Taiwan Univ. (Taiwan); J. M. Hinckley, J. Singh, Univ. of Michigan (United States)

LEDS II

- 7602 1K **Development of high-power UV LEDs for epoxy curing applications (Invited Paper)** [7602-56]
W. H. Liu, C. F. Chu, C. C. Cheng, K. H. Hsu, Y. T. Chung, Y. K. Wang, C. C. Li, J. Y. Chu, F. H. Fan, H. C. Cheng, Y. W. Chen, Y. H. Chang, L. W. Shan, SemiLEDs Optoelectronics Corp. (Taiwan); T. Doan, C. Tran, SemiLEDs Corp. (United States)
- 7602 1L **Original GaIn-based LED structure on ZnO template by MOCVD** [7602-57]
R.-M. Lin, National Cheng Kung Univ. (Taiwan); S.-F. Yu, Chang Gung Univ. (Taiwan); M.-J. Chen, National Taiwan Univ. (Taiwan); W.-C. Hsu, Sino-American Silicon Products Inc. (Taiwan)
- 7602 1M **Enhancement of light extraction efficiency of blue-light-emitting diodes by moth-eye structure** [7602-58]
T. Kondo, A. Suzuki, F. Teramae, T. Kitano, Y. Kaneko, EL-SEED Corp. (Japan); R. Kawai, K. Teshima, S. Maeda, Meijo Univ. (Japan); S. Kamiyama, Meijo Univ. (Japan) and EL-SEED Corp. (Japan); M. Iwaya, H. Amano, I. Akasaki, Meijo Univ. (Japan)

- 7602 1N **Internal quantum efficiency of m-plane InGaN on Si and GaN** [7602-59]
J. Lee, X. Ni, M. Wu, X. Li, R. Shimada, Ü. Özgür, A. A. Baski, H. Morkoç, Virginia Commonwealth Univ. (United States); T. Paskova, G. Mulholland, K. R. Evans, Kyma Technologies, Inc. (United States)

LEDS III

- 7602 1R **Efficiency retention at high current injection levels in m-plane InGaN light emitting diodes** [7602-63]
X. Li, X. Ni, J. Lee, M. Wu, Ü. Özgür, H. Morkoç, Virginia Commonwealth Univ. (United States); T. Paskova, G. Mulholland, K. R. Evans, Kyma Technologies, Inc. (United States)

POSTER SESSION

- 7602 1W **Ab initio study of structural properties for zincblende AlInN: comparison of LDA and GGA** [7602-68]
B.-T. Liou, Hsiuping Institute of Technology (Taiwan); B.-Y. Wu, De-Lin Institute of Technology (Taiwan)
- 7602 1X **Output power enhancement of light-emitting diodes with defect passivation layer** [7602-69]
M.-H. Lo, P.-M. Tu, National Chiao Tung Univ. (Taiwan); Y.-J. Cheng, National Chiao Tung Univ. (Taiwan) and Research Ctr. for Applied Sciences, Academia Sinica (Taiwan); C.-H. Wang, C.-W. Hung, National Chiao Tung Univ. (Taiwan); S.-C. Hsu, Tamkang Univ. (Taiwan); H.-C. Kuo, H.-W. Zan, S.-C. Wang, C.-Y. Chang, National Chiao Tung Univ. (Taiwan); C.-M. Liu, Sino-American Silicon Products Inc. (Taiwan)
- 7602 20 **Non-polar m-plane GaN on patterned Si(112) substrates by metalorganic chemical vapor deposition** [7602-73]
X. Ni, M. Wu, J. Lee, X. Li, A. Baski, Ü. Özgür, H. Morkoç, Virginia Commonwealth Univ. (United States)
- 7602 21 **Comparison of different template structures for high quality and self-separation thick GaN growth** [7602-74]
Y.-H. Fang, C.-L. Chao, T.-W. Chi, K.-M. Chen, P.-C. Liu, J.-D. Tsay, Industrial Technology Research Institute (Taiwan)
- 7602 22 **Analytical methods to study loss mechanisms and lifetime investigations of blue InGaN laser diodes** [7602-75]
J. Müller, G. Bröderl, M. Schillgalies, A. Breidenassel, S. Tautz, D. Dini, T. Lerner, S. Lutgen, U. Strauß, OSRAM Opto Semiconductors GmbH (Germany)
- 7602 23 **Reduction in operating voltage of UV laser diode** [7602-76]
T. Ichikawa, K. Takeda, Y. Ogiso, K. Nagata, M. Iwaya, S. Kamiyama, H. Amano, I. Akasaki, Meijo Univ. (Japan); H. Yoshida, M. Kuwabara, Y. Yamashita, H. Kan, Hamamatsu Photonics K.K. (Japan)
- 7602 24 **On carrier spillover in c- and m-plane InGaN light-emitting diodes** [7602-77]
J. Lee, X. Li, X. Ni, Ü. Özgür, H. Morkoç, Virginia Commonwealth Univ. (United States); T. Paskova, G. Mulholland, K. R. Evans, Kyma Technologies, Inc. (United States)

- 7602 25 **Analysis and comparison of UV photodetectors based on wide bandgap semiconductors**
[7602-78]
Q. Wang, S. Savage, B. Noharet, I. Petermann, S. Persson, S. Almqvist, M. Bakowski,
J. Y. Andersson, Acreo AB (Sweden) and IMAGIC Ctr. (Sweden)

Author Index

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- 1 Growth I
Hadis Morkoç, Virginia Commonwealth University (United States)
- 2 Growth II
Alois J. Krost, Otto-von-Guericke-Universität Magdeburg (Germany)
- 3 Growth III
Cole W. Litton, Air Force Research Laboratory - retired (United States)
- 4 FETs
Peter H. Handel, University of Missouri-St. Louis (United States)
- 5 FET Reliability
Yasushi Nanishi, Ritsumeikan University (Japan)
- 6 Advanced Techniques I
Shigefusa F. Chichibu, Tohoku University (Japan)
- 7 Advanced Techniques II
Russell D. Dupuis, Georgia Institute of Technology (United States)
- 8 QW and Dots
Sandra Ruffenach, Université Montpellier 2 (France)
- 9 Lasers
Dong-Seon Lee, Gwangju Institute of Science and Technology (Korea, Republic of)
- 10 Novel Devices
Joachim Piprek, NUSOD Institute LLC (United States)
- 11 Poster Highlight
Hadis Morkoç, Virginia Commonwealth University (United States)
- 12 LEDs I
Avery Liu, SemiLEDs Corporation (United States)
- 13 LEDs II
Ferdinand Scholz, Universität Ulm (Germany)
- 14 LEDs III
Hidetō Miyake, Mie University (Japan)
- 15 LEDs IV
Jen-Inn Chyi, National Central University (Taiwan)

Dedication

Dr. Cole W. Litton

It is with great honor and the deepest sadness that we dedicate these proceedings to the memory of **Cole W. Litton** who passed away while attending the conference on January 26, 2010, shortly after the completion of the last session that day. He cherished every aspect of organizing the conference and if he were to use a narrative for his passing it might not have been much different from what actually took place. The solace that we can all draw from this, if there is one, is that he passed on while doing what he loved most.

Dr. Litton started the series on Gallium Nitride Materials and Devices in 1996 and took care of all that had to be done on his own as his co-chair that year, Hadis Morkoç, was involuntarily committed to a myriad of other must do duties and could not be of much help. It is worth noting that the proceedings of the first Gallium Nitride Materials and Devices series was dedicated to commemorate the occasion of the retirement of his and our long time colleague Dr. G. L. Witt after many decades of service to the research community. Cole had dedicated himself to research and development as researcher and program manager, and also to his colleagues for many decades, in particular to his younger colleagues as they navigated through the complex web of science and engineering.

On the personal side, he was a kind and caring individual who never seemed to lose his composure under any circumstances. He will surely be missed by many whom he directly and indirectly touched, and will be affected by the absence of calming presence and guidance.

Introduction

GaN based electronic and optoelectronic devices continue to develop rapidly as reflected by the advances reported at the meeting. Today, the GaN based light emitters adorn the automobiles, traffic lights, moving signs, outdoor displays, handheld electronics, and background lighting in many consumer electronics including flat panel televisions. All LED outdoor lighting applications are already in full swing. Indoor lighting with LEDs seems to be the frontier that GaN seems surely conquering with all manufacturers being under capacity due to increasing demand. The wall-plug efficiencies in excess of 50% at brightness levels needed for lighting certainly bode well for GaN based LEDs. Efficiency retention or the loss of it at high injection levels has received a great deal of attention due to the enormous impact of efficiency on indoor lighting by LEDs. To the end, non polar and semi-polar orientations of GaN and InGaN in the context of growth and investigations of optical processes are in full swing. Due to cost pressures, Si substrates for GaN epitaxy with clever patterning and strain balancing, to avoid cracking upon cooling from growth temperatures, being implemented. Measurement of internal quantum efficiency has been recognized to be an important step in the LED development for many years and the issue has come to the forefront in relation to GaN based LEDs as indicated by presentations and discussions on the topic.

The last year's program featured a good deal of shorter wavelength LEDs for medical applications, skin ailment treatment, curing of polymers, and applications such as water purification as well as short range communication are also being developed. The conference this year was representative of this push, but also a push for longer wavelengths for lasers as well as LEDs. The latter application is in part driven by lighting applications in case the tri-color approach, using red, green and blue LEDs, is used for general lighting applications.

Switching gears to FETs, the last year's program had a good deal of focus on both high power RF and switching applications of GaN based FETs and other three terminal devices. This year the focus centered on the carrier transport and the associated scattering mechanisms, the routes for heat dissipation from hot electrons to the heat sink. It was reported that the enhanced coupling of hot electrons with LO phonons and inability in general for LO phonons to LA phonons lead to high density of hot phonons with equivalent temperatures in the range of 2000 K, much like the hot electrons. With participation of plasmons, particularly at carrier densities corresponding to the plasma frequency that is resonant with GaN LO phonon energy efficient decay of LO phonons was noted and used to enhance carrier velocity and also improve reliability of FETs. Also introduced was

the use of low frequency noise measurement to measure the degree of degradation in FETs. These measurements were noted to be much more sensitive to degradation as compared to e.g. I-V measurements. Many devices, particularly FETs, are sensitive to surfaces and their preparation. Surface charge sensitive probes used to view not only the surface of GaN but also its evolution when subjected to various ambient conditions.

The SPIE symposium on GaN Materials and Devices is annually organized to disseminate the latest results and provide an opportunity for researchers from around the world to engage in far reaching and probing discussions. Many world renowned invited speakers from Asia, Europe and USA set the stage with wide ranging formal discussions. Not to be underestimated is the fact that the meeting served the purpose of getting experts and newcomers together for friendship and informal discussions of issues relevant to GaN and related materials and devices, and also to develop collaborations. Such exchanges will undoubtedly play an invaluable role in the propelling the field forward in general and in particular addressing pivotal issues such as determination and improvement of internal quantum efficiency in GaN and related materials and external quantum efficiency.

Cole W. Litton (*deceased*)
Jen-Inn Chyi
Yasushi Nanishi
Hadis Morkoç
Joachim Piprek
Euijoon Yoon